



# GPT200

## FAST RECOVERY DIODE BRIDGE

### TARGET SPECIFICATION

Fast recovery time characteristics

Insulated base

**VOLTAGE UP TO 600 V**

**DC OUTPUT CURRENT 60 A**

### BLOCKING CHARACTERISTICS

Characteristic	Conditions	Value
$V_R$	Repetitive cathode to anode voltage	600 V
$I_{RRM}$	Repetitive peak reverse current, max.	$V_R$ , single phase, half wave, $T_j = T_{jmax}$
$V_{ISOL}$	RMS insulation voltage	Any terminals to case, $t = 1$ min

### FORWARD CHARACTERISTICS

$I_F$	Maximum DC output current	$T_c = 85^\circ C$	60 A
$I_{FSM}$	Surge forward current	Single pulse, $T_j = 25^\circ C$	300 A
$V_{F(TO)}$	Threshold voltage	$T_j = T_{jmax}$	0,914 V
$r_F$	Forward slope resistance	$T_j = T_{jmax}$	10,5 m $\Omega$
$V_{FM}$	Peak forward voltage, max	Forward current $I_F = 30$ A, $T_j = T_{jmax}$	1,23 V

### SWITCHING CHARACTERISTICS

$Q_{rr}$	Reverse recovery charge, typ	$T_j = 25^\circ C$ , $I_F = 20$ A, $di/dt = -100$ A/ $\mu s$ $V_R = 30$ V	1,2 nC
$I_{rr}$	Reverse recovery current		10 A
$t_{rr}$	Reverse recovery time, typ		160 ns

### THERMAL AND MECHANICAL CHARACTERISTICS

$R_{th(j-c)}$	Thermal resistance (junction to case)	Both leg conduction	0,4 $^\circ C/W$
$T_{jmax}$	Max operating junction temperature		150 $^\circ C$
$F$	Mounting torque		1,3 N·m
	Mass		30 g